

SuperCDMS Compton step calibration study

SuperCDMS collaboration

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WNPPC

2024



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@SuperCDMS

Direct search for dark matter

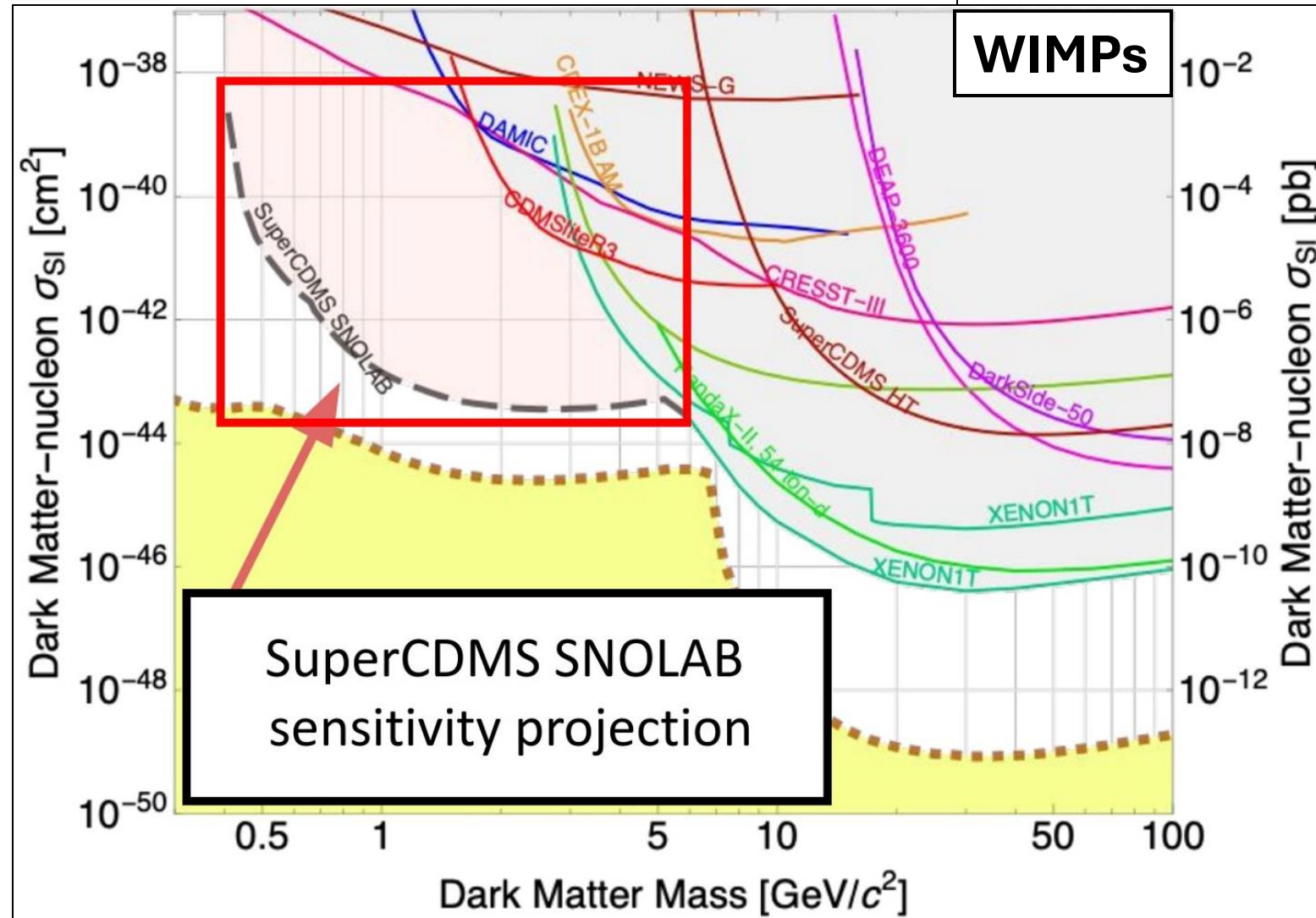
Goal:

- Observe or reject dark matter models.

Procedure:

- Dark matter model.
- Background model.
- Experiment data.
- A statistical test.
- Any indication for dark matter in data?

First need detector calibration.

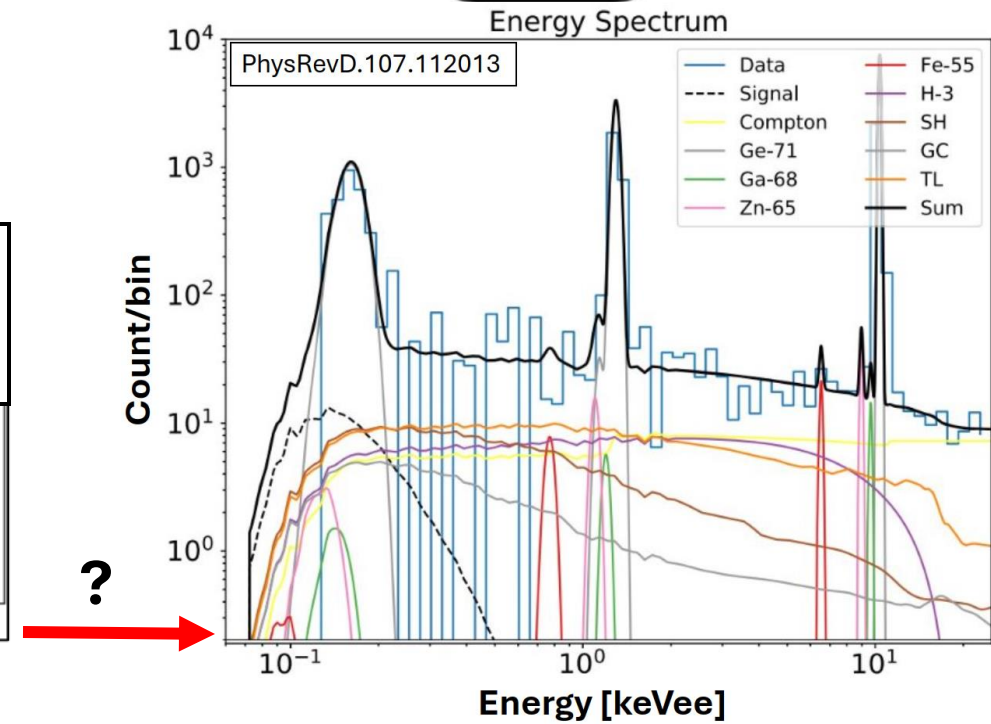
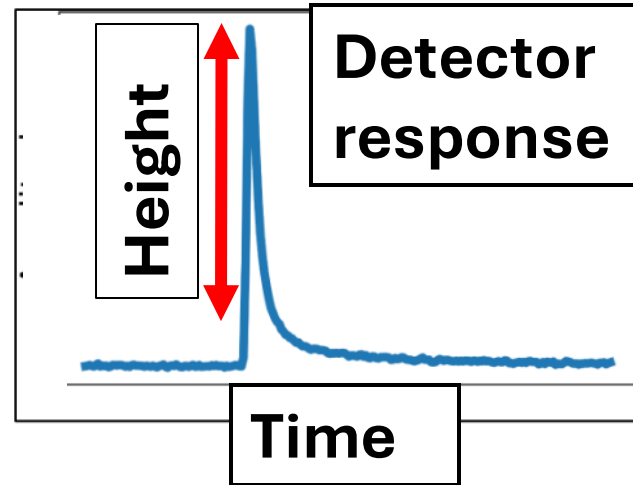
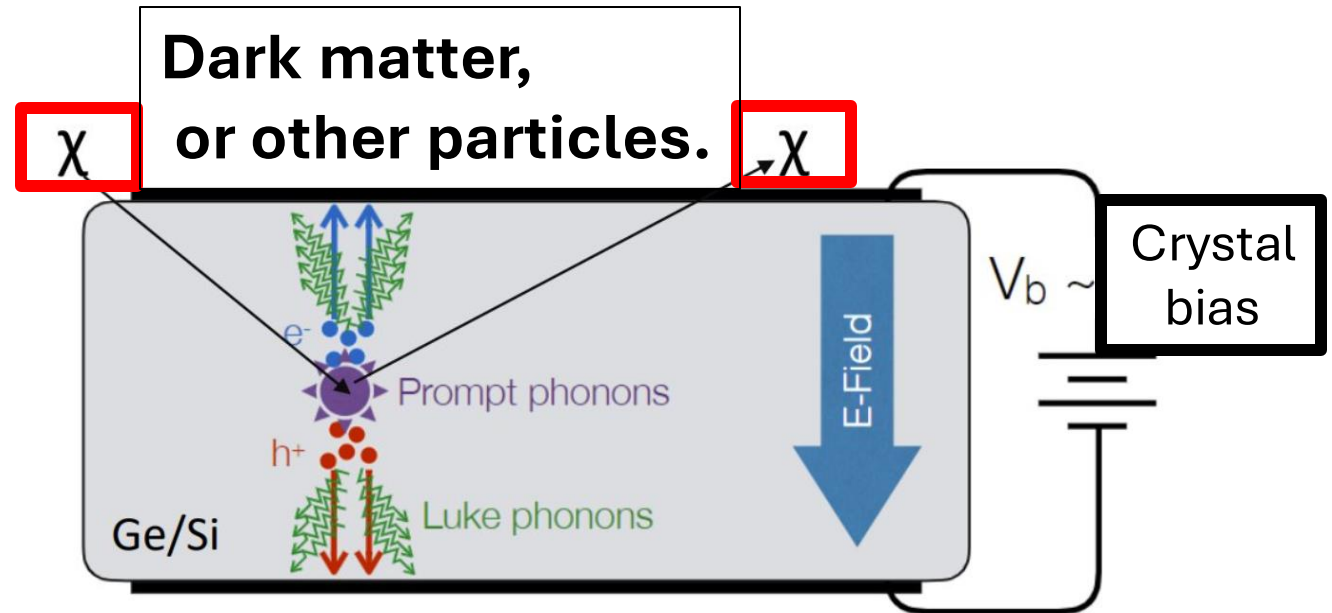


What is calibration

- Choose calibration sources with signatures at known energies.
- Identify the signatures in data.
- Extract the calibration function.

Final goal:

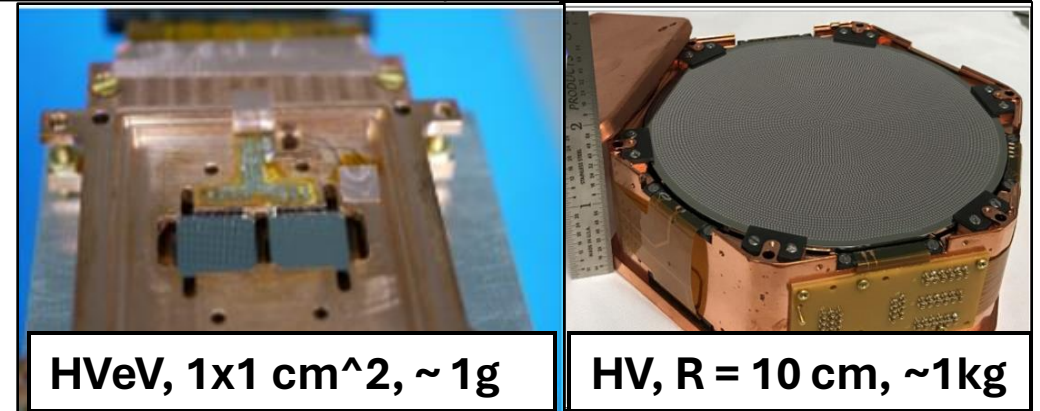
$$\text{Function}(\text{Height}) = \text{Energy}$$



Calibration methods

Energies		Low (few eV)	Intermediate (up to 10keV)	
Procedure		Optical photons	Compton steps	Intrinsic activation lines
Ge	HV (~10eV resolution)	✗	✗	✓
Si	HV (~10eV resolution)	✗	!	✗
	HVeV (~eV resolution)	✓	?	✗

- Today: **Si-HVeV** is under **investigation**. ?
- Future: **Si-HV** is the **final goal**. !

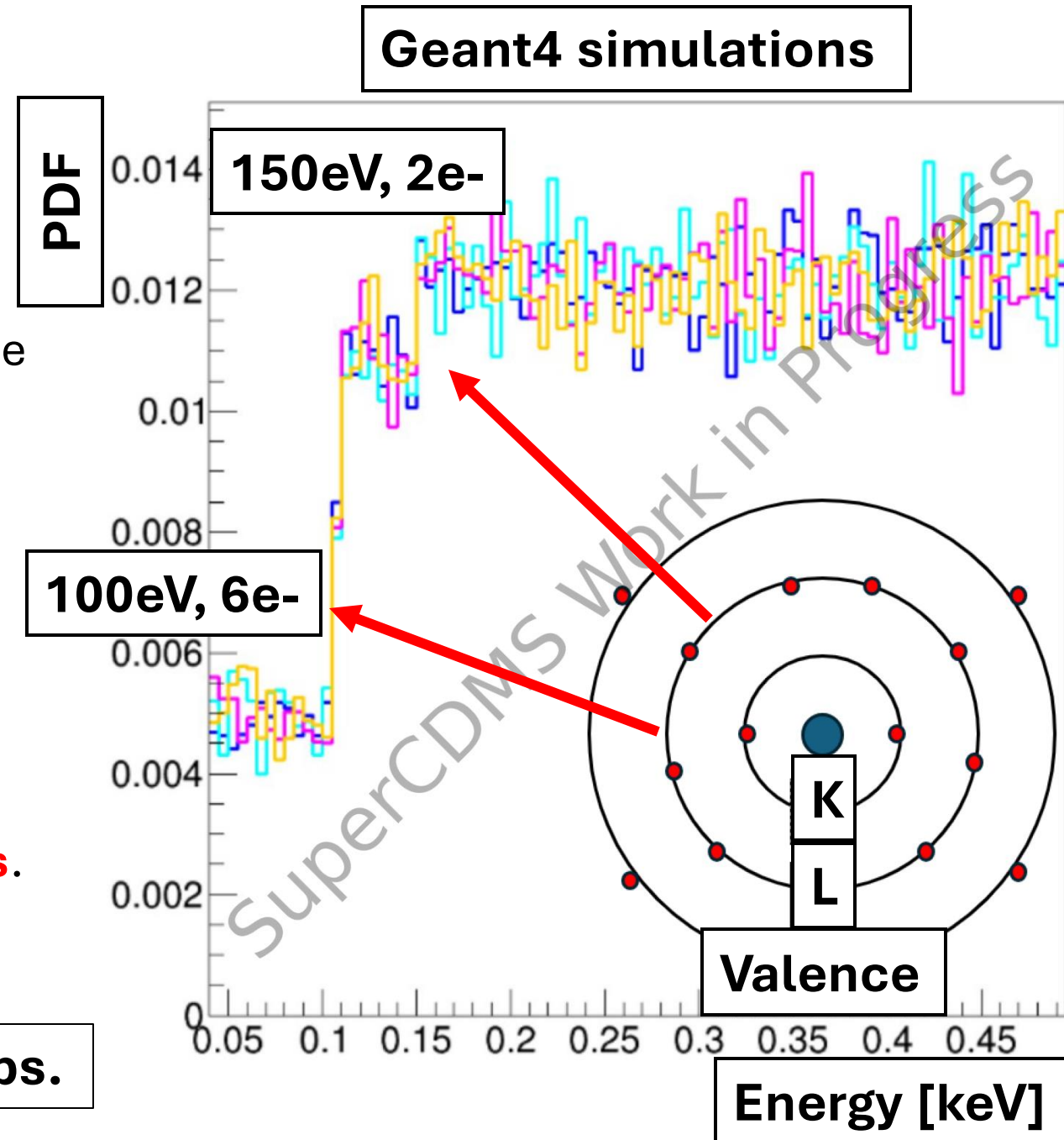


Silicon L-shell steps

Compton steps:

- Irradiate with O(100) keV gamma rays to produce Compton scatters.
- Electromagnetic interactions.
- The binding energy of the electron limits the minimum required energy for scattering.
- Scattering **probability** \propto # **accessible electrons**.

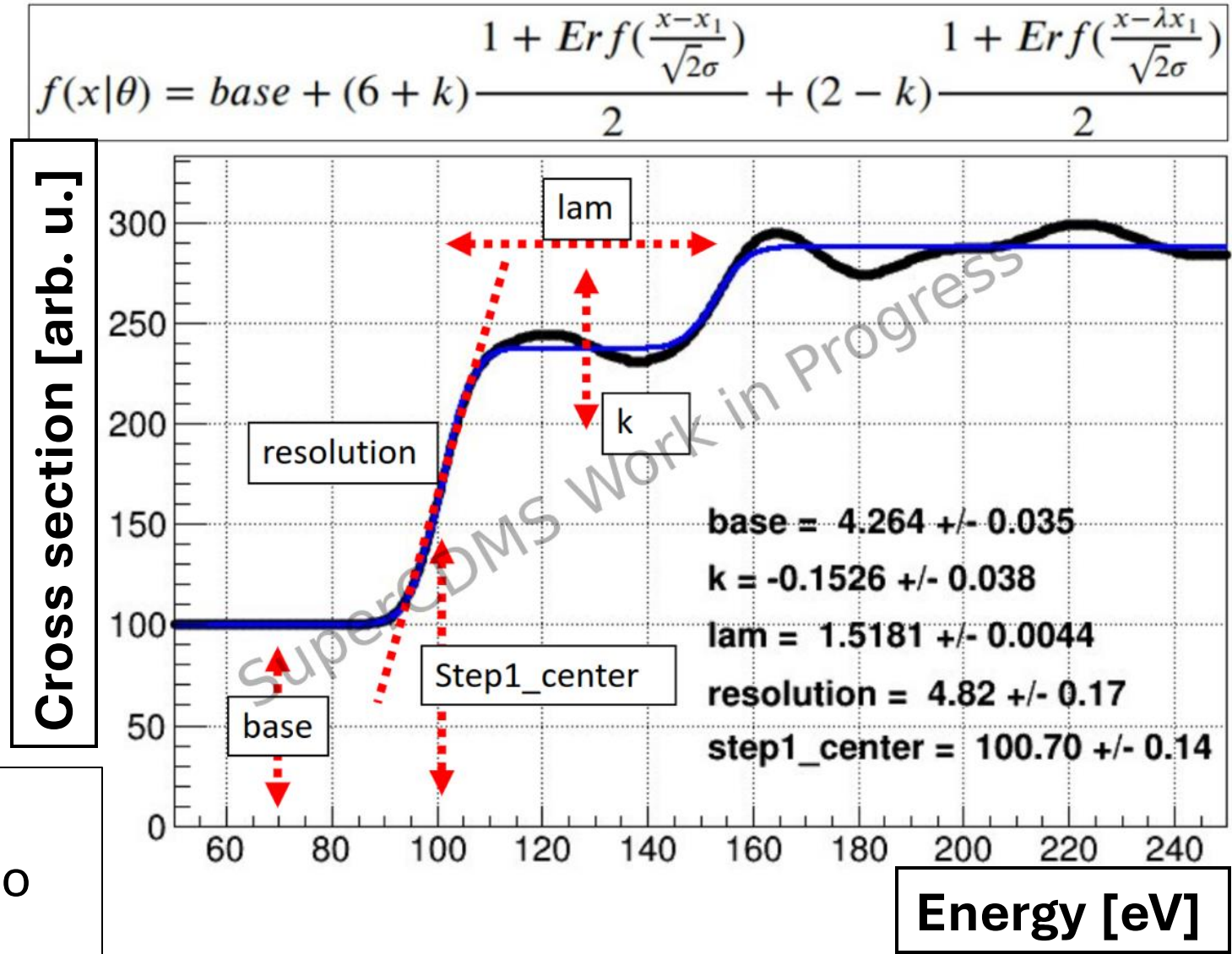
Right: L-step simulations, 2S and 2P steps.



L-shell calibration

1. Need a step detection system.
2. Perform simulations.
3. Take data.
4. Compare simulation to data.

Black line: **FEFF** simulation.
Blue line: **Analytical model** fitted to simulations.



L-shell simulations

Different simulation packages:

1. Geant4 simulations:

- Based on impulse approximation for E&M scatters.
- Not trustworthy near Compton steps.
- Monte Carlo based.

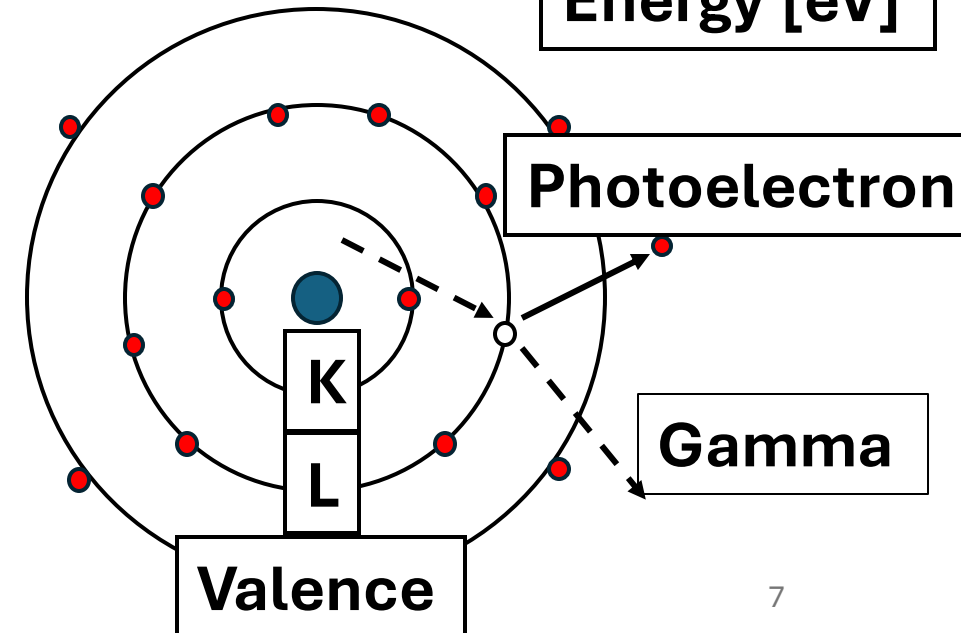
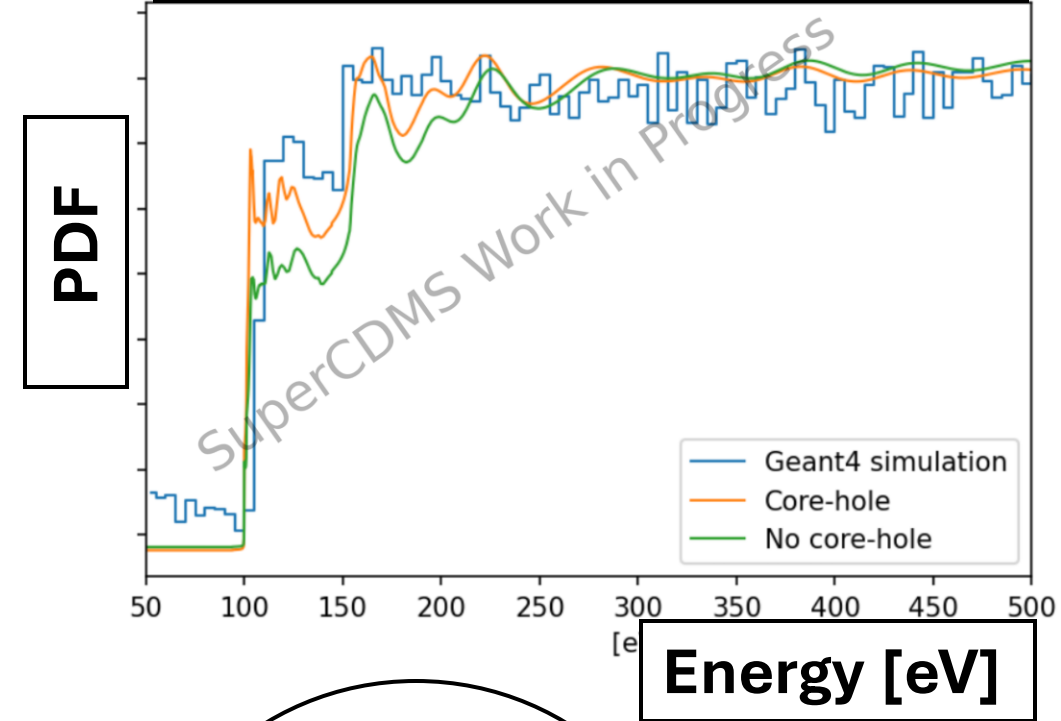
2. FEFF simulation:

- No impulse approximation.
- Deviates from Geant4 simulations.
- Ab initio calculation of cross section.

Impulse approximation:

- Ignore the **external potential** on the photoelectron **during the scattering** process.
- Valid when: **Transferred energy** \gg **Binding energy**.
- In other words: Scattering **time scale** \ll **Atomic response**.

Geant4 vs FEFF simulations



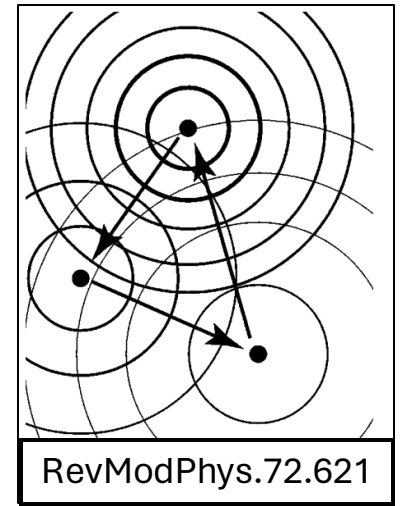
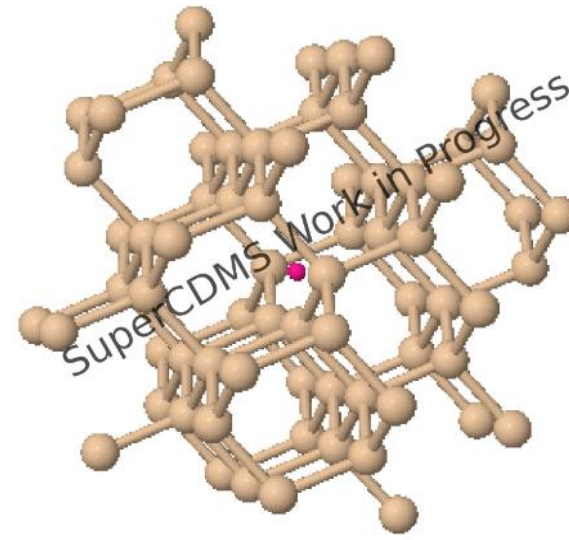
FEFF simulations

FEFF calculations:

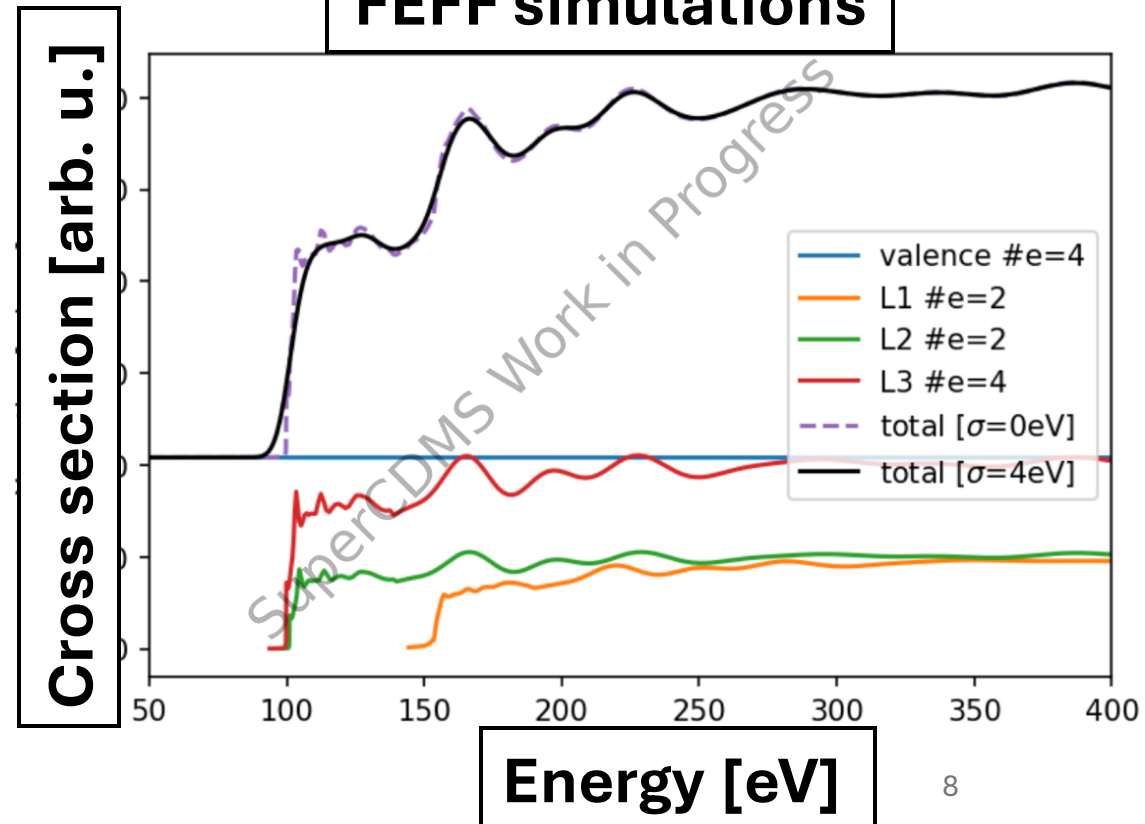
- Model the external potential on the photoelectron.
- Thus, need the arrangement of atoms. (Si crystal)
- And a target atom. (Pink dot)
- Each electron shell -> Separate Calculation.

Cross section **oscillation** in FEFF:

Constructive and **destructive interference** patterns of the **photoelectron** wave **depending** on **wavelength** and **atomic spacing** (top right).



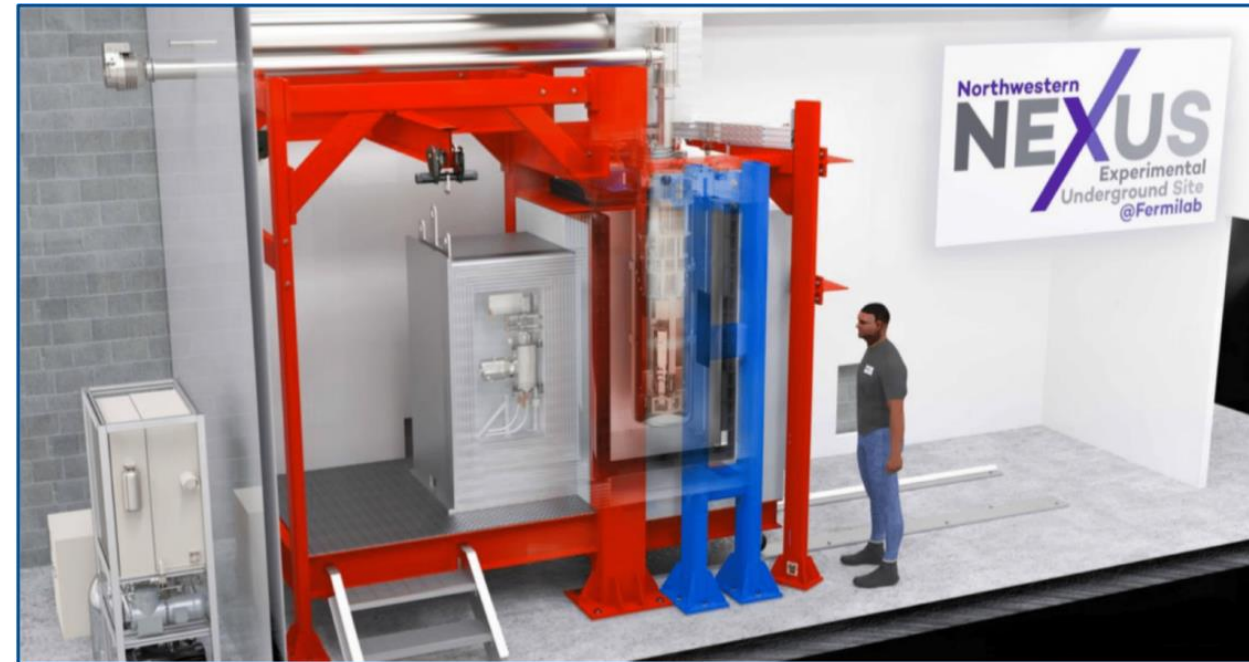
FEFF simulations



Compton calibration data

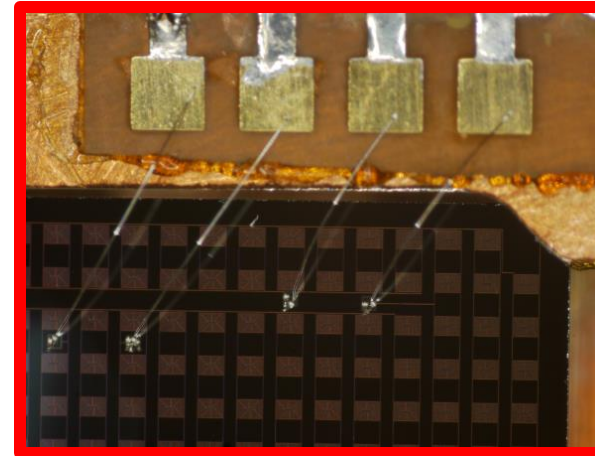
Compton step Calibration data:

- Facility: NEXUS at Fermilab.
- Overburden: 100m.
- Detectors: Si-HVeV prototype/R&D.
- Calibration source: Cs-137 (662keV gamma rays).

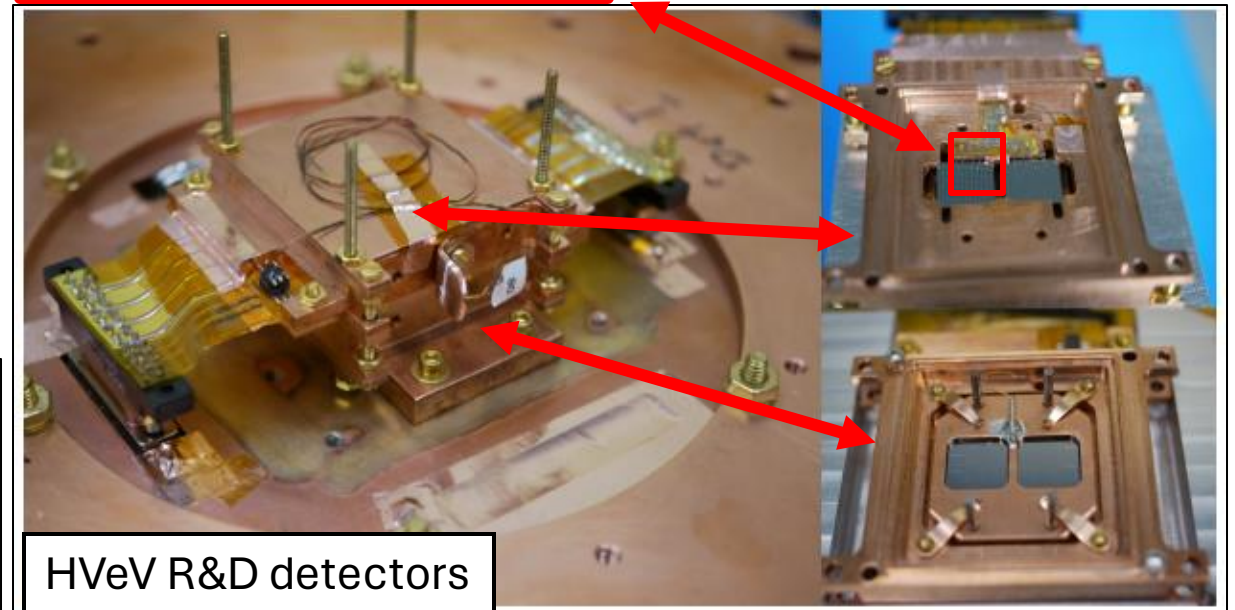


Next steps

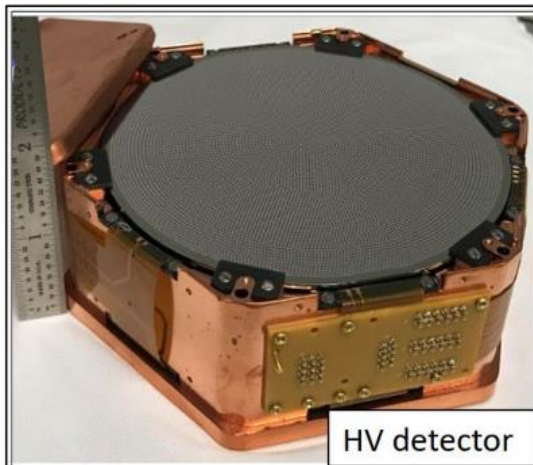
- Compton step analysis for HVeV detectors is going through SuperCDMS internal review. (Oops, no data today!)
- Looking forward to use the developed calibration scheme for HV detectors.



HVeV
10x10x4 mm³
Silicon
~1g



HVeV R&D detectors



R = 10cm, H=3cm
Silicon or germanium
~1kg

HV detector

Thanks!



@SuperCDMS



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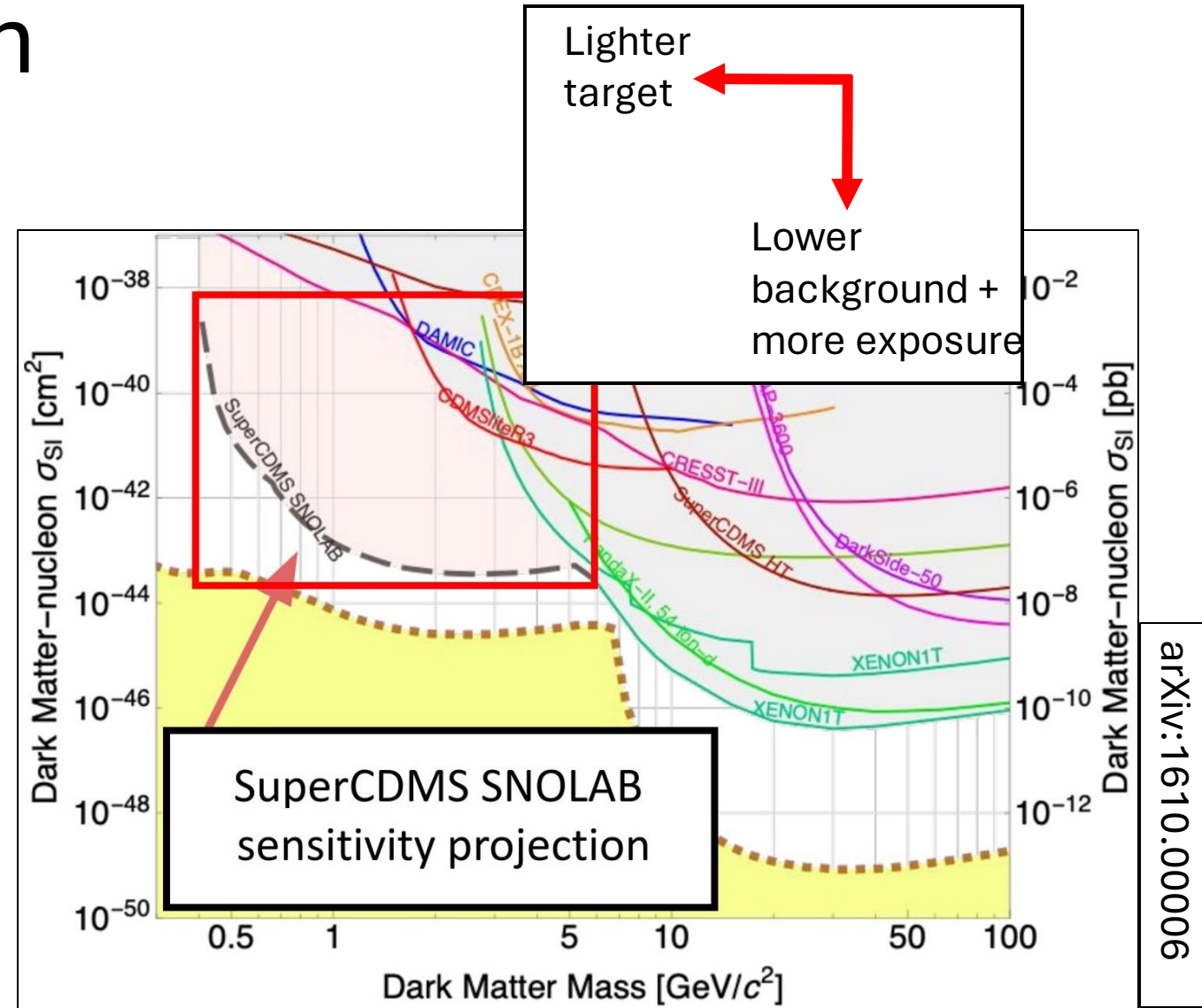
Backup

WIMP direct detection

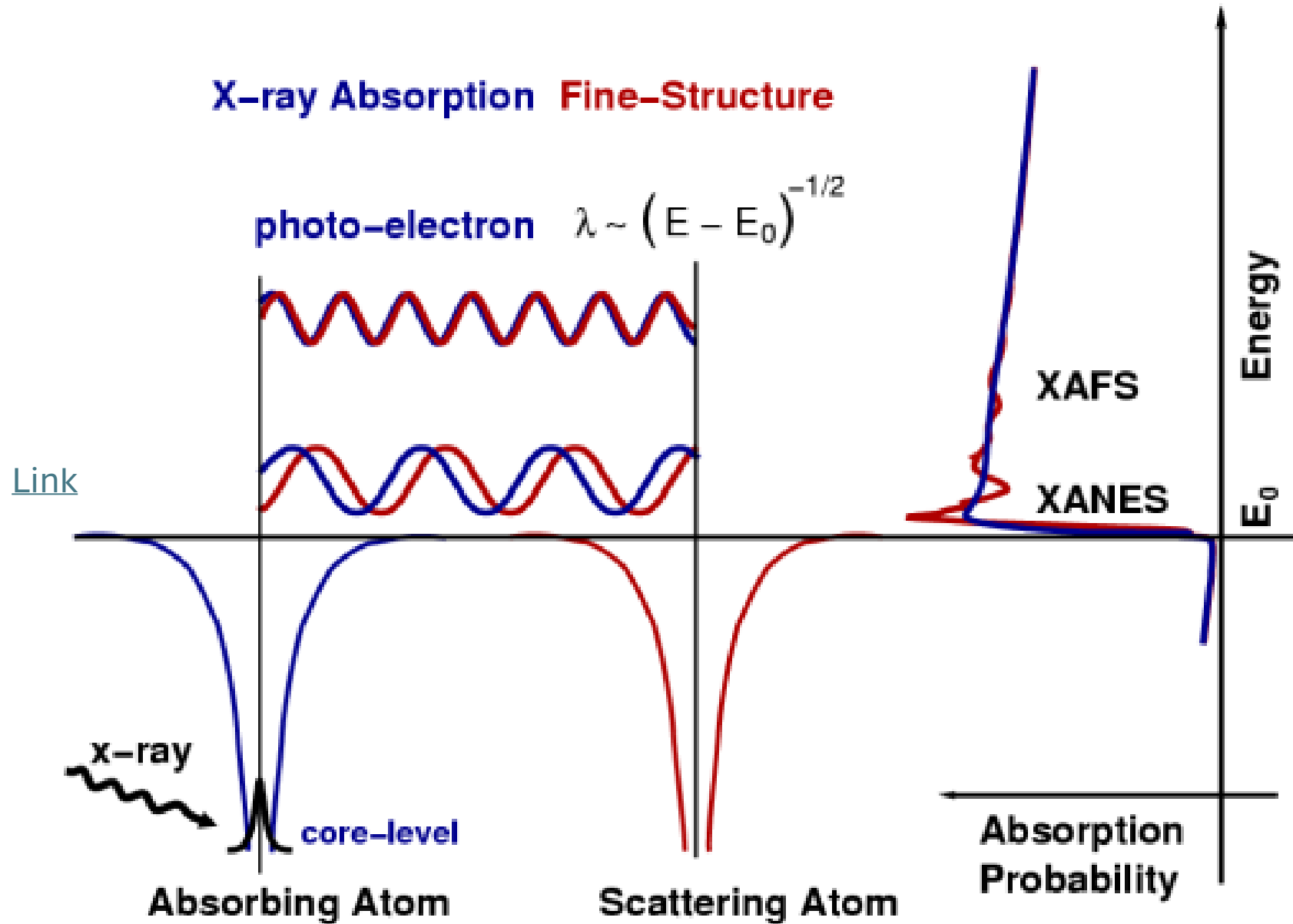
Cryogenic semiconductor detectors:

- Assuming known backgrounds.
- More exposure \rightarrow Lower cross section.
- More sensitive detector \rightarrow Lower mass.

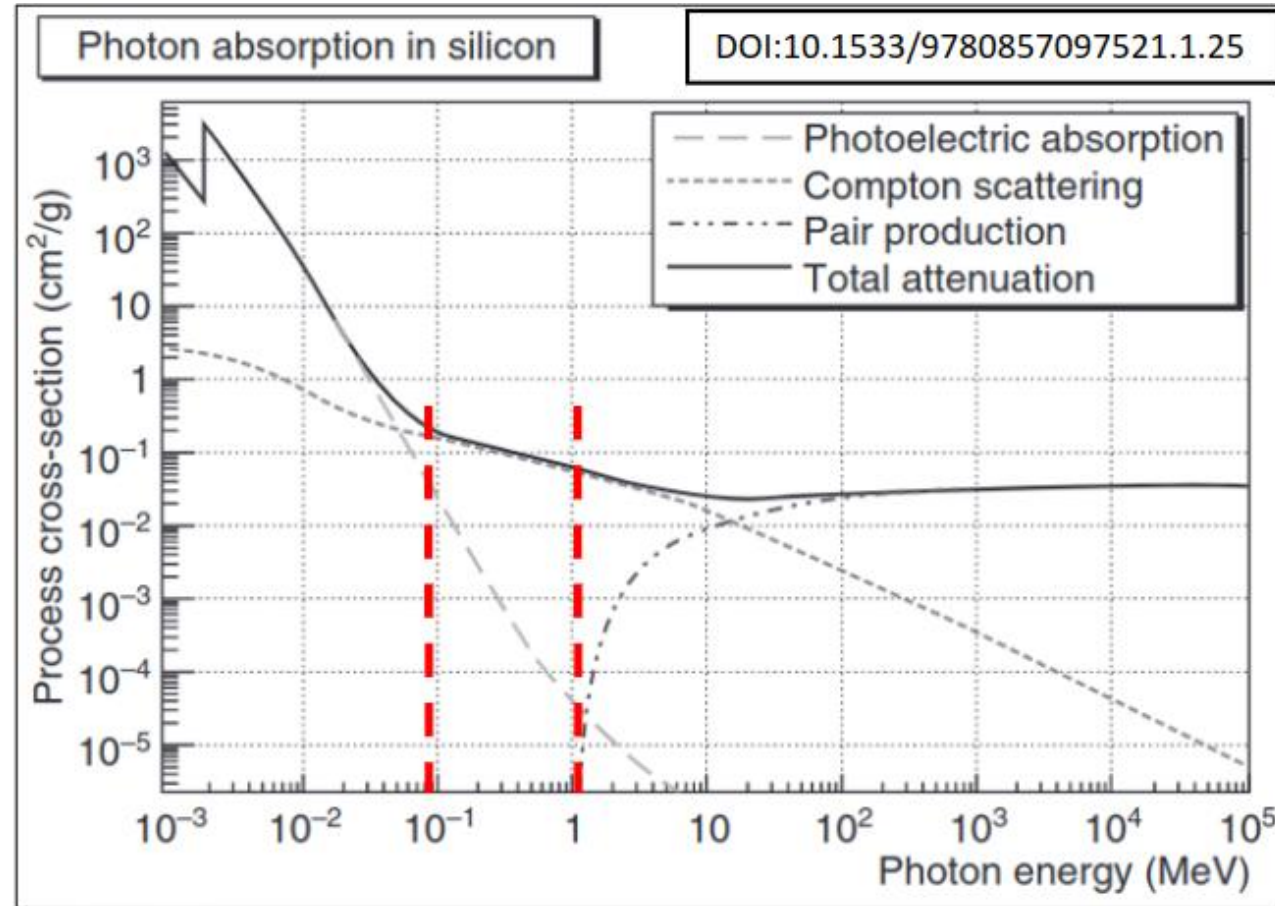
First need detector calibration.



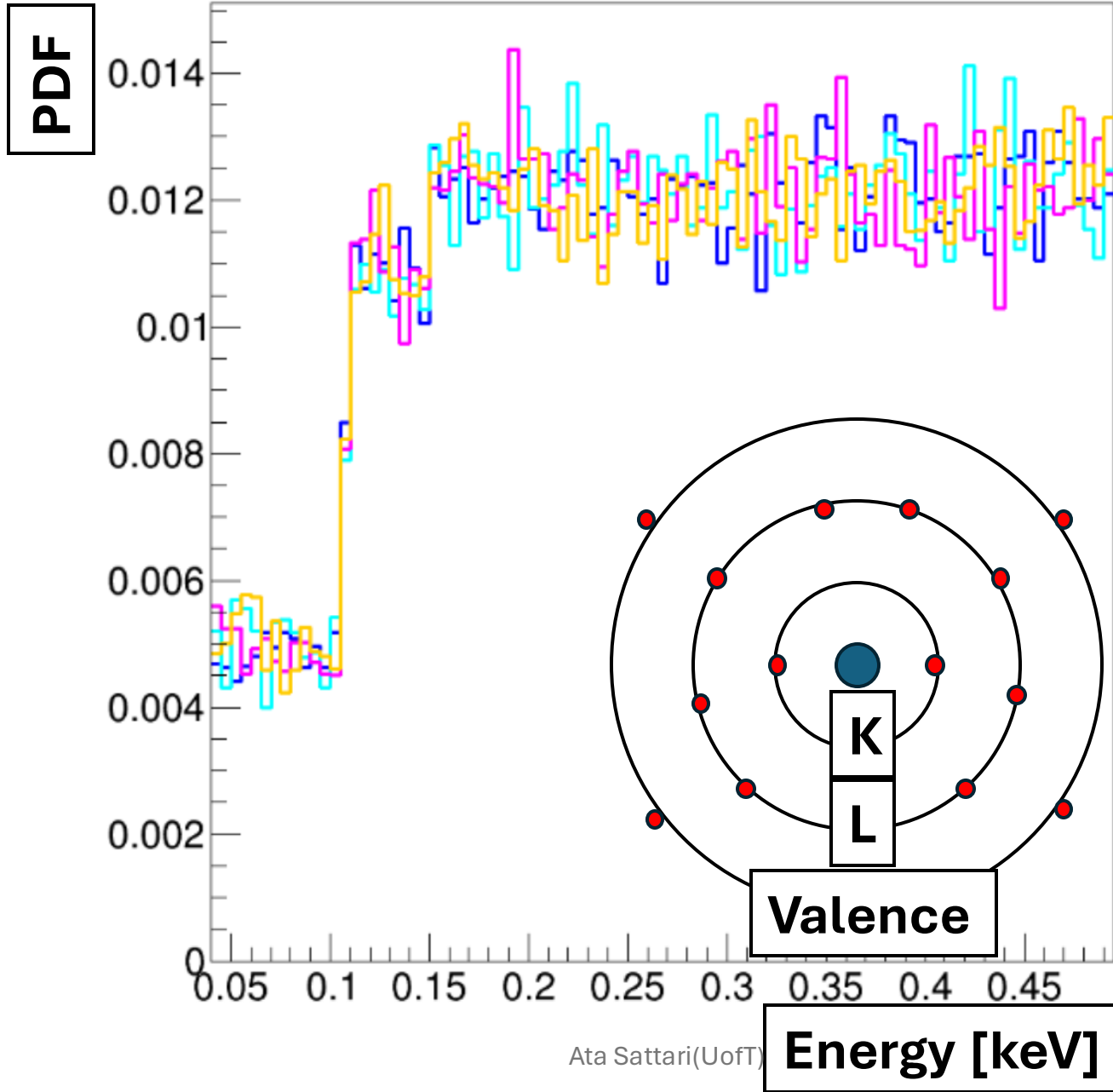
X-ray Absorption Fine-Structure



Silicon absorption length



L-Steps: 100eV, 150eV



Geant4 geometry

